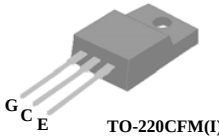
Advanced Power Electronics Corp.

N-CHANNEL INSULATED GATE BIPOLAR TRANSISTOR

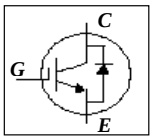
Features

- ▼ **High Speed Switching**
- ▼ **Low Saturation Voltage**
  $V_{CE(sat),typ.}$=1.7V@I_C=12A
- ▼ **RoHS Compliant Product**



TO-220CFM(I)

V_{CES}	600V
I_C	12A



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{CES}	Collector-Emitter Voltage	600	V
V_{GE}	Gate-Emitter Voltage	±20	V
I_C@T_C=25°C	Collector Current	25	A
I_C@T_C=100°C	Collector Current	12	A
I_{CM}	Pulsed Collector Current[1]	50	A
I_F@T_C=100°C	Diode Forward Current	8	A
I_{FM}	Diode Pulse Forward Current	40	A
P_D@T_C=25°C	Maximum Power Dissipation	33	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	150	°C

Notes:

1.Pulse width limited by Max. junction temperature .

Thermal Data

Symbol	Parameter	Value	Units
Rthj-c	Thermal Resistance Junction-Case	3.8	°C/W
Rthj-c(Diode)	Thermal Resistance Junction-Case	5	°C/W
Rthj-a	Thermal Resistance Junction-Ambient	65	°C/W

Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
I_{GES}	Gate-to-Emitter Leakage Current	V_{GE}=±20V, V_{CE}=0V	-	-	±100	nA
I_{CES}	Collector-Emitter Leakage Current	V_{CE}=600V, V_{GE}=0V	-	-	1	mA
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	V_{GE}=15V, I_C=12A	-	1.7	2.2	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	V_{GE}=15V, I_C=25A	-	1.9	-	V
$V_{GE(th)}$	Gate Threshold Voltage	V_{CE}=V_{GE}, I_C=250uA	2	-	6	V
Q_g	Total Gate Charge	I_C=20A	-	95	150	nC
Q_{ge}	Gate-Emitter Charge	V_{CC}=480V	-	16	-	nC
Q_{gc}	Gate-Collector Charge	V_{GE}=15V	-	35	-	nC
$t_{d(on)}$	Turn-on Delay Time	V_{CE}=480V,	-	40	-	ns
t_r	Rise Time	I_c=20A,	-	20	-	ns
$t_{d(off)}$	Turn-off Delay Time	V_{GE}=15V,	-	140	-	ns
t_f	Fall Time	R_G=5Ω,	-	200	400	ns
E_{on}	Turn-On Switching Loss	Inductive Load	-	0.1	-	mJ
E_{off}	Turn-Off Switching Loss		-	1	-	mJ
C_{ies}	Input Capacitance	V_{GE}=0V	-	2760	4400	pF
C_{oes}	Output Capacitance	V_{CE}=30V	-	65	-	pF
C_{res}	Reverse Transfer Capacitance	f=1.0MHz	-	40	-	pF

V_F	FRD Forward Voltage	I_F=8A	-	1.8	2.4	V
t_{rr}	FRD Reverse Recovery Time	I_F=8A	-	30	-	ns
Q_{rr}	FRD Reverse Recovery Charge	di/dt = 100 A/μs	-	30	-	nC

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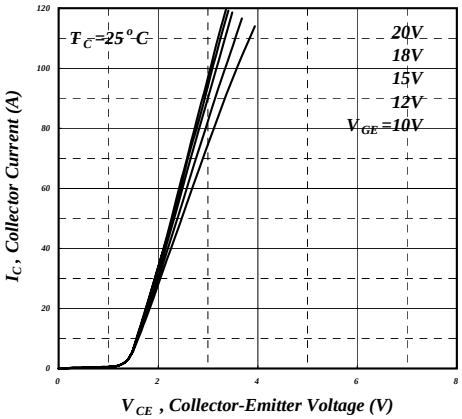

Fig 1. Typical Output Characteristics

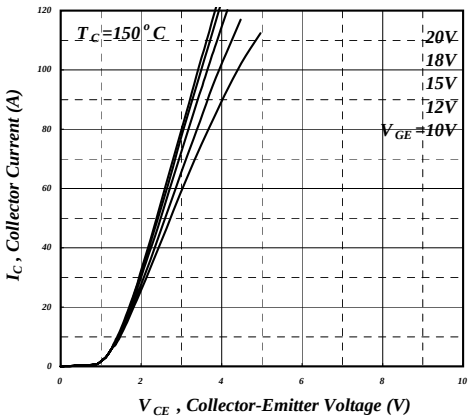

Fig 2. Typical Output Characteristics

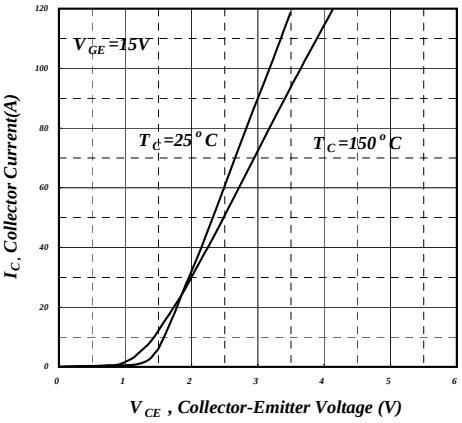

Fig 3. Typical Saturation Voltage Characteristics

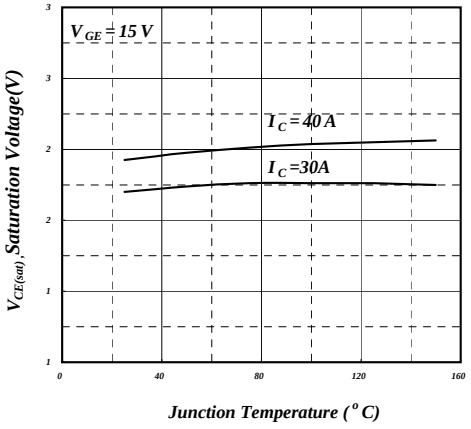

Fig 4. Typical Collector- Emitter Voltage v.s. Junction Temperature

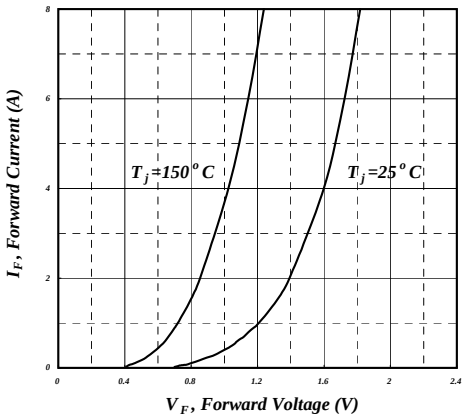

Fig 5. Forward Characteristic of Diode

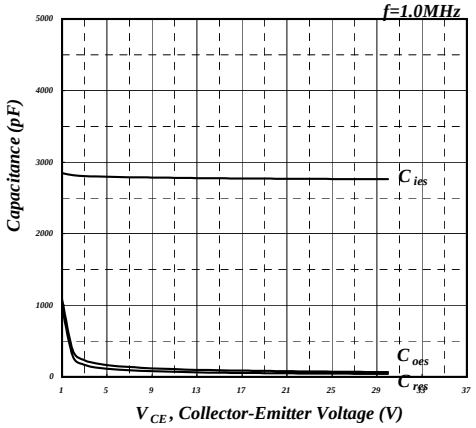

Fig 6. Typical Capacitance Characterisitics

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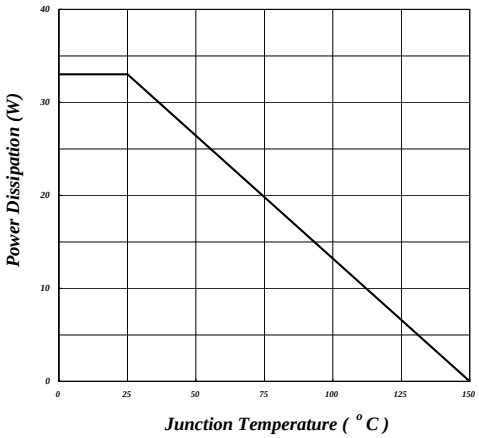

Fig7. Power Dissipation vs. Junction Temperature

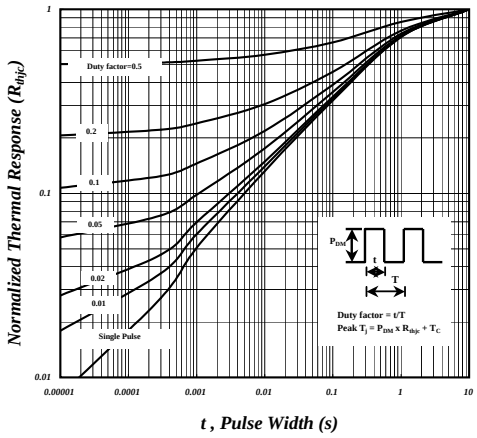

Fig 8. Effective Transient Thermal Impedance

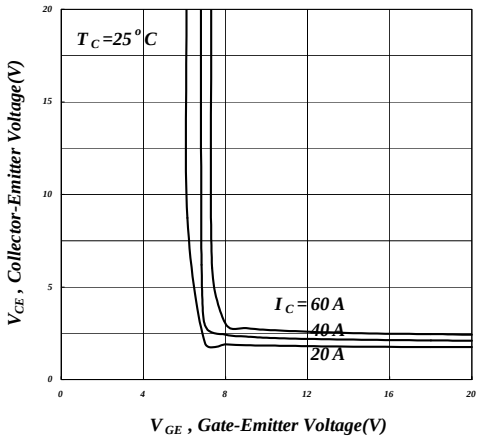

Fig 9. Saturation Voltage vs. V_{GE}

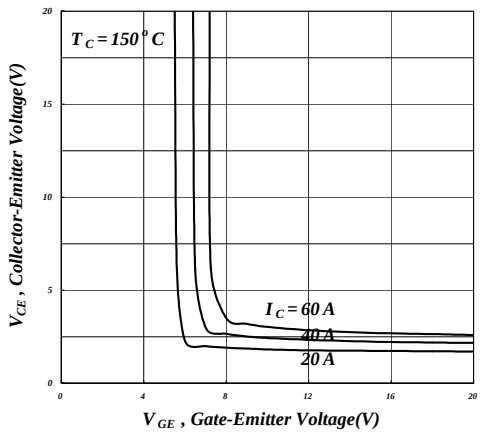

Fig 10. Saturation Voltage vs. V_{GE}

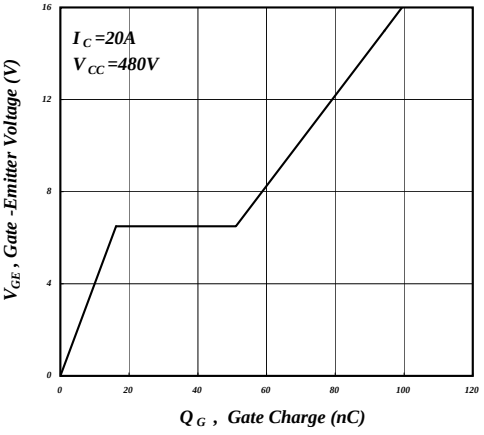

Fig 11. Gate Charge Characterisitics

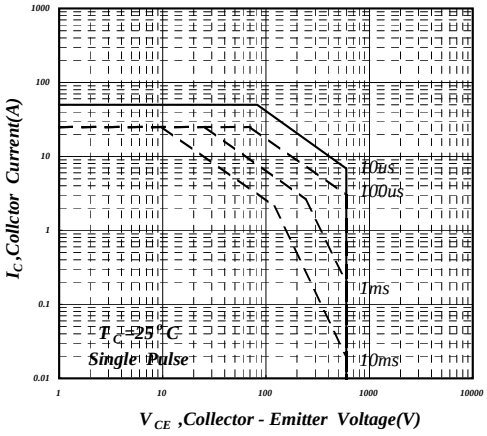

Fig 12. SOA Characteristics

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